# INTEGRATED CIRCUITS

# DATA SHEET

# **74LVC2G08**Dual 2-input AND gate

**Product specification** 

2003 Aug 25





# **Dual 2-input AND gate**

74LVC2G08

#### **FEATURES**

- Wide supply voltage range from 1.65 to 5.5 V
- 5 V tolerant inputs and outputs for interfacing with 5 V logic
- · High noise immunity
- Complies with JEDEC standard:
  - JESD8-7 (1.65 to 1.95 V)
  - JESD8-5 (2.3 to 2.7 V)
  - JESD8B/JESD36 (2.7 to 3.6 V)
- ±24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- · Direct interface with TTL levels
- · Inputs accept voltages up to 5 V
- SOT505-2 package
- ESD protection:
  - HBM EIA/JESD22-A114-A exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
- Specified from -40 to +85 °C and -40 to +125 °C.

#### **DESCRIPTION**

The 74LVC2G08 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{\text{off}}$ . The  $I_{\text{off}}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC2G08 provides the 2-input AND gate.

#### **QUICK REFERENCE DATA**

GND = 0 V;  $T_{amb} = 25 \, ^{\circ}C$ ;  $t_r = t_f \le 2.5 \, \text{ns}$ .

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay inputs nA, nB to	$V_{CC} = 1.8 \text{ V}; C_L = 30 \text{ pF}; R_L = 1 \text{ k}\Omega$	3.2	ns
	outputs nY	$V_{CC} = 2.5 \text{ V}; C_L = 30 \text{ pF}; R_L = 500 \Omega$	2.2	ns
		$V_{CC} = 2.7 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	2.5	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	2.1	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	1.7	ns
C <sub>I</sub>	input capacitance		2.5	pF
C <sub>PD</sub>	power dissipation capacitance per gate	V <sub>CC</sub> = 3.3 V; notes 1 and 2	14.4	pF

#### **Notes**

1.  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

 $f_i$  = input frequency in MHz;

 $f_0$  = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts;

N = total load switching outputs;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$ 

2. The condition is  $V_1 = GND$  to  $V_{CC}$ .

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#### **FUNCTION TABLE**

See note 1.

INF	OUTPUT	
nA	nB	nY
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

#### Note

1. H = HIGH voltage level;

L = LOW voltage level.

#### **ORDERING INFORMATION**

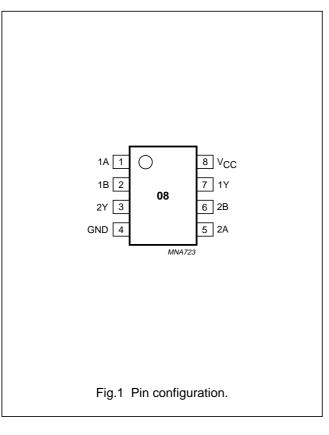
	PACKAGE							
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING		
74LVC2G08DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	V08		

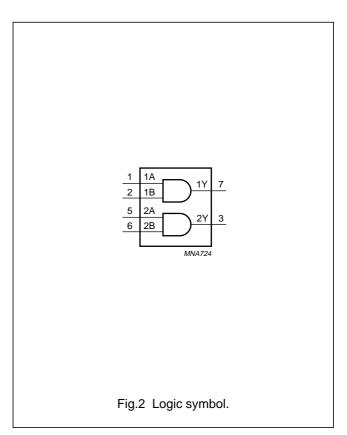
#### **PINNING**

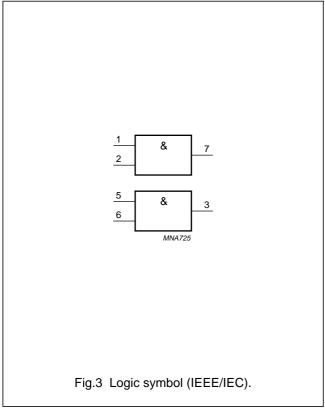
PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1B	data input
3	2Y	data output
4	GND	ground (0 V)
5	2A	data input
6	2B	data input
7	1Y	data output
8	V <sub>CC</sub>	supply voltage

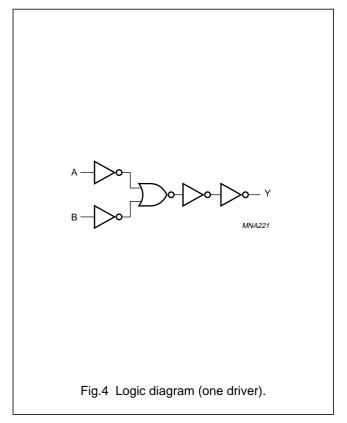
# Dual 2-input AND gate

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#### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	active mode	0	V <sub>CC</sub>	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	5.5	V
T <sub>amb</sub>	operating ambient temperature		-40	+125	°C
t <sub>r</sub> , t <sub>f</sub>	input rise and fall times	V <sub>CC</sub> = 1.65 to 2.7 V	0	20	ns/V
		V <sub>CC</sub> = 2.7 to 5.5 V	0	10	ns/V

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		-0.5	+6.5	V
I <sub>IK</sub>	input diode current	V <sub>I</sub> < 0	_	-50	mA
VI	input voltage	note 1	-0.5	+6.5	V
I <sub>OK</sub>	output diode current	V <sub>O</sub> > V <sub>CC</sub> or V <sub>O</sub> < 0	- ±50		mA
Vo	output voltage	active mode; notes 1 and 2	-0.5	V <sub>CC</sub> + 0.5	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
Io	output source or sink current	$V_O = 0$ to $V_{CC}$	_	±50	mA
I <sub>CC</sub> , I <sub>GND</sub>	V <sub>CC</sub> or GND current		_	±100	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>D</sub>	power dissipation	$T_{amb} = -40 \text{ to } +125 ^{\circ}\text{C}$	_	300	mW

#### Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. When  $V_{CC} = 0 \text{ V}$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

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#### **DC CHARACTERISTICS**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	DADAMETED	TEST CONDITIONS			TVD	BAAY	
SYMBOL	PARAMETER	OTHER	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	UNIT
T <sub>amb</sub> = -40	) to +85 °C; note 1		-		'	•	1
V <sub>IH</sub>	HIGH-level input voltage		1.65 to 1.95	$0.65 \times V_{CC}$	_	_	V
			2.3 to 2.7	1.7	_	_	٧
			2.7 to 3.6	2.0	_	_	٧
			4.5 to 5.5	$0.7 \times V_{CC}$	_	_	٧
V <sub>IL</sub>	LOW-level input voltage		1.65 to 1.95	_	_	$0.35 \times V_{CC}$	٧
			2.3 to 2.7	_	_	0.7	٧
			2.7 to 3.6	_	_	0.8	V
			4.5 to 5.5	_	_	$0.3 \times V_{CC}$	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$					
		I <sub>O</sub> = 100 μA	1.65 to 5.5	_	_	0.1	V
		I <sub>O</sub> = 4 mA	1.65	_	0.08	0.45	V
		$I_O = 8 \text{ mA}$	2.3	_	0.14	0.3	V
		I <sub>O</sub> = 12 mA	2.7	_	0.19	0.4	V
		I <sub>O</sub> = 24 mA	3.0	_	0.37	0.55	V
		I <sub>O</sub> = 32 mA	4.5	_	0.43	0.55	V
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$					
	voltage	$I_{O} = -100 \mu\text{A}$	1.65 to 5.5	V <sub>CC</sub> - 0.1	_	_	V
		$I_O = -4 \text{ mA}$	1.65	1.2	1.53	_	V
		$I_O = -8 \text{ mA}$	2.3	1.9	2.13	_	V
		$I_0 = -12 \text{ mA}$	2.7	2.2	2.50	_	V
		$I_0 = -24 \text{ mA}$	3.0	2.3	2.60	_	V
		$I_{O} = -32 \text{ mA}$	4.5	3.8	4.10	_	V
ILI	input leakage current	$V_I = 5.5 \text{ V or GND}$	5.5	_	±0.1	±5	μΑ
I <sub>off</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$	0	_	±0.1	±10	μΑ
Icc	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	0.1	10	μΑ
$\Delta I_{CC}$	additional quiescent supply current per pin	$V_{I} = V_{CC} - 0.6 \text{ V};$ $I_{O} = 0$	2.3 to 5.5	_	5	500	μΑ

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SYMBOL	DAD AMETED	TEST COND	ITIONS		T\/D	BAAN/	
SYMBOL	PARAMETER	OTHER	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	UNIT
T <sub>amb</sub> = -40	) to +125 °C		'	1	'	•	!
V <sub>IH</sub>	HIGH-level input voltage		1.65 to 1.95	0.65 × V <sub>CC</sub>	_	_	V
			2.3 to 2.7	1.7	_	_	V
			2.7 to 3.6	2.0	_	_	V
			4.5 to 5.5	$0.7 \times V_{CC}$	_	_	V
V <sub>IL</sub>	LOW-level input voltage		1.65 to 1.95	_	_	$0.35 \times V_{CC}$	V
			2.3 to 2.7	_	_	0.7	V
			2.7 to 3.6	_	_	0.8	V
			4.5 to 5.5	_	_	$0.3 \times V_{CC}$	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$					
		I <sub>O</sub> = 100 μA	1.65 to 5.5	_	_	0.10	V
		I <sub>O</sub> = 4 mA	1.65	_	_	0.70	V
		I <sub>O</sub> = 8 mA	2.3	_	_	0.45	V
		I <sub>O</sub> = 12 mA	2.7	_	_	0.60	V
		I <sub>O</sub> = 24 mA	3.0	_	_	0.80	V
		I <sub>O</sub> = 32 mA	4.5	_	_	0.80	V
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$					
	voltage	$I_{O} = -100  \mu A$	1.65 to 5.5	V <sub>CC</sub> – 0.1	_	_	V
		$I_O = -4 \text{ mA}$	1.65	0.95	_	_	V
		$I_O = -8 \text{ mA}$	2.3	1.7	_	_	V
		$I_{O} = -12 \text{ mA}$	2.7	1.9	_	_	V
		$I_{O} = -24 \text{ mA}$	3.0	2.0	_	_	V
		$I_{O} = -32 \text{ mA}$	4.5	3.4	_	_	V
ILI	input leakage current	V <sub>I</sub> = 5.5 V or GND	5.5	_	_	±20	μΑ
I <sub>off</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$	0	_	_	±20	μΑ
I <sub>CC</sub>	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	_	40	μΑ
$\Delta I_{CC}$	additional quiescent supply current per pin	$V_{I} = V_{CC} - 0.6 \text{ V};$ $I_{O} = 0$	2.3 to 5.5	-	_	5000	μА

#### Note

1. All typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25  $^{\circ}C.$ 

# Dual 2-input AND gate

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#### **AC CHARACTERISTICS**

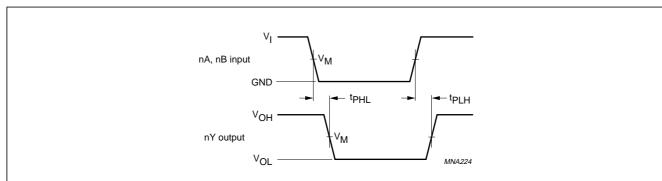
GND = 0 V

CVMDOL	DADAMETED	TEST COND	TEST CONDITIONS		MIN TVD	MAY	LINUT
SYMBOL	PARAMETER	WAVEFORMS	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	UNIT
T <sub>amb</sub> = -40	to +85 °C; note 1						
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay	see Figs 5 and 6	1.65 to 1.95	1.0	3.2	9.0	ns
inputs nA, nB to outputs nY		2.3 to 2.7	0.5	2.2	5.1	ns	
		2.7	1.0	2.5	5.3	ns	
			3.0 to 3.6	0.5	2.1	4.7	ns
			4.5 to 5.5	0.5	1.7	3.8	ns
T <sub>amb</sub> = -40 f	to +125 °C						
t <sub>PHL</sub> /t <sub>PLH</sub>	propagation delay	see Figs 5 and 6	1.65 to 1.95	1.0	_	11.3	ns
	inputs nA, nB to outputs nY		2.3 to 2.7	0.5	_	6.4	ns
			2.7	1.0	_	6.7	ns
			3.0 to 3.6	0.5	_	5.9	ns
			4.5 to 5.5	0.5	_	4.8	ns

#### Note

1. All typical values are measured at  $T_{amb}$  = 25 °C.

#### **AC WAVEFORMS**



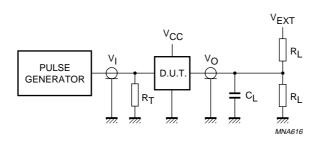
V	V	INPUT			
V <sub>CC</sub>	V <sub>M</sub>	VI	$t_r = t_f$		
1.65 to 1.95 V	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 2.0 ns		
2.3 to 2.7 V	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 2.0 ns		
2.7 V	1.5 V	2.7 V	≤ 2.5 ns		
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns		
4.5 to 5.5 V	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 2.5 ns		

 $\ensuremath{V_{\text{OL}}}$  and  $\ensuremath{V_{\text{OH}}}$  are typical output voltage drop that occur with the output load.

Fig.5 The inputs nA, nB to outputs nY propagation delay and the output transition times.

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V	V.	C	D.	V <sub>EXT</sub>
V <sub>CC</sub>	V <sub>I</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PLH</sub> /t <sub>PHL</sub>
1.65 to 1.95 V	V <sub>CC</sub>	30 pF	1 kΩ	open
2.3 to 2.7 V	V <sub>CC</sub>	30 pF	500 Ω	open
2.7 V	2.7 V	50 pF	500 Ω	open
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open
4.5 to 5.5 V	V <sub>CC</sub>	50 pF	500 Ω	open

Definitions for test circuit:

R<sub>L</sub> = Load resistor.

 $\ensuremath{C_L}$  = Load capacitance including jig and probe capacitance.

 $R_{T} = Termination$  resistance should be equal to the output impedance  $Z_{\text{o}}$  of the pulse generator.

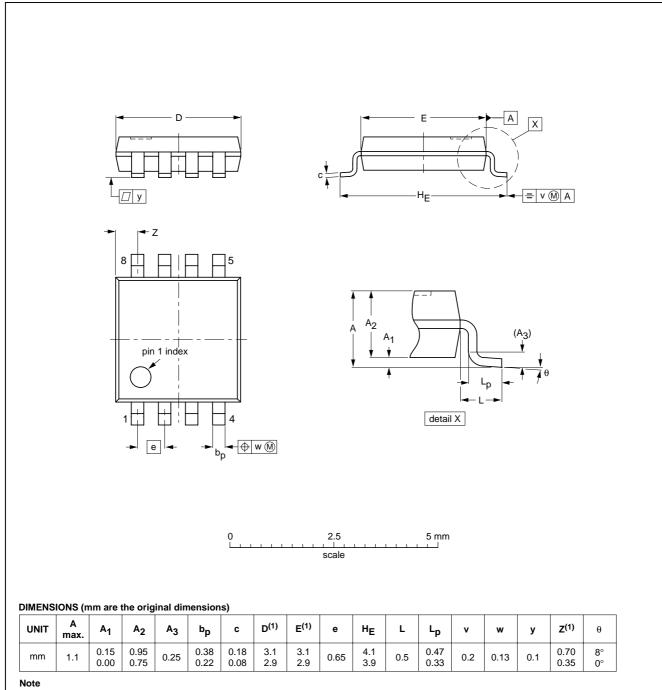
Fig.6 Load circuitry for switching times.

# Dual 2-input AND gate

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#### **PACKAGE OUTLINE**

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES		EUROPEAN	ICCUE DATE
VERSION	IEC	IEC JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT505-2						02-01-16

#### **Dual 2-input AND gate**

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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